

Kentaroh Watanabe

List of Publications by Year in descending order

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145
docs citations

145
times ranked

1190
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoabsorption improvement in multi-stacked InGaAs/GaAs quantum dot solar cell with a light scattering rear texture. <i>Solar Energy Materials and Solar Cells</i> , 2020, 204, 110216.	3.0	9
2	Modeling and design for low-cost multijunction solar cell via light-trapping rear texture technique: Applied in InGaP/GaAs/InGaAs triple junction. <i>Progress in Photovoltaics: Research and Applications</i> , 2020, 28, 251-265.	4.4	11
3	Identification of surface and volume hot-carrier thermalization mechanisms in ultrathin GaAs layers. <i>Journal of Applied Physics</i> , 2020, 128, 193102.	1.1	17
4	Efficient Perovskite Solar Modules with Minimized Nonradiative Recombination and Local Carrier Transport Losses. <i>Joule</i> , 2020, 4, 1263-1277.	11.7	93
5	Comparison of Effective Carrier Mobility Between Wire on Well and Planar Superlattice Using Time-of-Flight Measurement. <i>IEEE Journal of Photovoltaics</i> , 2020, 10, 1008-1014.	1.5	3
6	High-Speed MOVPE Growth of InGaP Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2020, 10, 480-486.	1.5	9
7	Fabrication and optical characterization of ultrathin III-V transferred heterostructures for hot-carrier absorbers. , 2020, , .		2
8	Design of concentrator multijunction solar modules for UV-LED disinfection of water in off-the-grid areas. , 2020, , .		0
9	Current transport efficiency analysis of multijunction solar cells by luminescence imaging. <i>Progress in Photovoltaics: Research and Applications</i> , 2019, 27, 835-843.	4.4	4
10	24.5% efficient GaAs p-on-n solar cells with 120 μm MOVPE growth. <i>Journal of Applied Physics</i> , 2019, 125, 105501.	1.3	7
11	Spatially Resolved Identification of Shunt Defects in Thin Film Solar Cells via Current Transport Efficiency Imaging Combined with 3D Finite Element Modeling. <i>Solar Rrl</i> , 2019, 3, 1800342.	3.1	9
12	Epitaxial Lift-Off of Ultrathin Heterostructures for Hot-Carrier Solar Cell Applications. , 2019, , .		0
13	High throughput MOVPE and accelerated growth rate of GaAs for PV application. <i>Journal of Crystal Growth</i> , 2019, 509, 87-90.	0.7	3
14	Light absorption enhancement in ultra-thin layers for hot-carrier solar cells: first developments towards the experimental demonstration of an enhanced hot-carrier effect with light trapping. , 2019, , .		0
15	Effective mobility map for InGaP/InGaP multiple quantum-well-based solar cells. , 2019, , .		0
16	Accelerated GaAs growth through MOVPE for low-cost PV applications. <i>Journal of Crystal Growth</i> , 2018, 489, 63-67.	0.7	8
17	Growth of InGaAs(P) in planetary metalorganic vapor phase epitaxy reactor using tertiarybutylarsine and tertiarybutylphosphine for photovoltaic applications. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 08RD09.	0.8	9
18	Solar to Hydrogen Conversion using Concentrated Multi-junction Photovoltaics and Distributed Micro-Converter Architecture. , 2018, , .		5

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19	Transport efficiency imaging in multi-junction solar cells by luminescence analysis. , 2018, , .		4
20	Carrier Collection Improvement in InGaAs/GaAsN Multiple Quantum Well Solar Cell with Flat Conduction Band. , 2018, , .		1
21	Comparison of Effective Carrier Mobility between Wire on Well and Multiple Quantum Well by Time of Flight Measurement. , 2018, , .		1
22	Evaluation of the compensation ratio of heavily-Ga doped Ge for far-infrared detectors in astronomy. Japanese Journal of Applied Physics, 2018, 57, 116701.	0.8	1
23	Extremely High-Speed GaAs Growth by MOVPE for Low-Cost PV Application. IEEE Journal of Photovoltaics, 2018, , 1-8.	1.5	8
24	Thin-film multiple-quantum-well solar cells fabricated by epitaxial lift-off process. Japanese Journal of Applied Physics, 2018, 57, 08RF03.	0.8	4
25	Characterization of InGaAs/GaAsN multiple quantum well with flat conduction band for improving carrier transport in multijunction solar cell. , 2018, , .		0
26	Characterisation of multi-junction solar cells by mapping of the carrier transport efficiency using luminescence emission. , 2017, , .		0
27	Development of GaAs//Si current-balanced dual junction solar cell integrated by surface-activated bonding. , 2017, , .		0
28	Electroluminescence-based quality characterization of quantum wells for solar cell applications. Journal of Crystal Growth, 2017, 464, 94-99.	0.7	8
29	Effects of various dopants on properties of GaAs tunneling junctions and p-i-n solar cells. Japanese Journal of Applied Physics, 2017, 56, 08MC11.	0.8	2
30	Design of free-barrier InGaAs/GaNAs multiple quantum well solar cells with 1.2 eV energy gap. Japanese Journal of Applied Physics, 2017, 56, 08MA04.	0.8	4
31	Stability and controllability of InGaAs/GaAsP wire-on-well (WoW) structure for multi-junction solar cells. Journal of Crystal Growth, 2017, 464, 86-93.	0.7	4
32	200nm-thick GaAs solar cells with a nanostructured silver mirror. , 2017, , .		0
33	Effect of low-V/III-ratio metalorganic vapor-phase epitaxy on GaAs solar cells. Japanese Journal of Applied Physics, 2017, 56, 08MC06.	0.8	5
34	Photovoltaic Array Differential Backside Exposure Conditions: Backsheet Degradation and Site Design. , 2017, , .		2
35	Analysis of Deposited Residues and Its Cleaning Process on GaAs Substrate after Epitaxial Lift-Off. , 2017, , .		0
36	Creation and Value of Synthetic High-Frequency Solar Inputs for Distribution System QSTS Simulations. , 2017, , .		3

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37	Design of InGaP/GaAs/InGaAs multi-junction cells with reduced layer thicknesses using light-trapping rear texture. , 2017, , .		0
38	Quantum wire-on-a-well (WoW) cell with long carrier lifetime for efficient carrier transport. Progress in Photovoltaics: Research and Applications, 2016, 24, 1606-1614.	4.4	22
39	200nm-Thick GaAs solar cells with a nanostructured silver mirror. , 2016, , .		6
40	Optical analysis of the photon recycling effect in InGaAs/GaAsP multiple quantum well solar cell with light trapping structure. , 2016, , .		3
41	Photocurrent collection mechanism and role of carrier distribution in p-i-n quantum well solar cells. , 2016, , .		1
42	Admittance spectroscopy analysis on the interfacial defect levels in the surface-activated bonding of GaAs. , 2016, , .		0
43	Quasi-Fermi level splitting evaluation based on electroluminescence analysis in multiple quantum-well solar cells for investigating cell performance under concentrated light. Proceedings of SPIE, 2016, , .	0.8	4
44	Effective drift mobility approximation in multiple quantum-well solar cell. , 2016, , .		4
45	Maskless fabrication of broadband antireflection nanostructures on glass surfaces. Journal of Optics (United Kingdom), 2016, 18, 064008.	1.0	4
46	(Invited) Analysis of Defect Levels at GaAs/GaAs Surface-Activated Bonding Interface for Multi-Junction Solar Cells. ECS Transactions, 2016, 75, 33-38.	0.3	0
47	Development of Blocked-Impurity-Band-Type Ge Detectors Fabricated with the Surface-Activated Wafer Bonding Method for Far-Infrared Astronomy. Journal of Low Temperature Physics, 2016, 184, 225-230.	0.6	20
48	Development for Germanium Blocked Impurity Band Far-Infrared Image Sensors with Fully-Depleted Silicon-On-Insulator CMOS Readout Integrated Circuit. Journal of Low Temperature Physics, 2016, 184, 217-224.	0.6	8
49	A Demonstration of TIA Using FD-SOI CMOS OPAMP for Far-Infrared Astronomy. Journal of Low Temperature Physics, 2016, 184, 449-453.	0.6	1
50	Experimental Demonstration of Optically Determined Solar Cell Current Transport Efficiency Map. IEEE Journal of Photovoltaics, 2016, 6, 528-531.	1.5	12
51	Absorption threshold extended to 1.15 eV using InGaAs/GaAsP quantum wells for over 50% efficient lattice-matched quad-junction solar cells. Progress in Photovoltaics: Research and Applications, 2016, 24, 533-542.	4.4	56
52	InGaAs/GaAsP quantum wells and wires for high-efficiency photovoltaic applications. , 2016, , .		0
53	Thin-film solar cells with InGaAs/GaAsP multiple quantum wells and a rear surface etched with light trapping micro-hole array. Japanese Journal of Applied Physics, 2015, 54, 08KA13.	0.8	2
54	Microscopic observation of carrier-transport dynamics in quantum-structure solar cells using a time-of-flight technique. Applied Physics Letters, 2015, 107, .	1.5	13

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55	Errata to "High-Aspect-Ratio Structures for Efficient Light Absorption and Carrier Transport in InGaAs/GaAsP Multiple Quantum Well Solar Cells" [Apr 13 859-867]. IEEE Journal of Photovoltaics, 2015, 5, 704-704.	1.5	0
56	Lattice-matched 3-junction cell with 1.2-eV InGaAs/GaAsP superlattice middle cell for improved current matching. , 2015, , .		1
57	Comparison of electron and hole mobilities in multiple quantum well solar cells using a time-of-flight technique. , 2015, , .		0
58	Concentrated photovoltaic electrochemical cell (CPEC): A route toward high-efficiency, cost-effective solar hydrogen production. , 2015, , .		2
59	Enhanced Light Trapping in Multiple Quantum Wells by Thin-Film Structure and Backside Grooves With Dielectric Interface. IEEE Journal of Photovoltaics, 2015, 5, 697-703.	1.5	24
60	Investigation of carrier collection in multi-quantum well solar cells by luminescence spectra analysis. , 2015, , .		1
61	Effect of Barrier Thickness on Carrier Transport Inside Multiple Quantum Well Solar Cells Under High-Concentration Illumination. IEEE Journal of Photovoltaics, 2015, 5, 846-853.	1.5	5
62	Effect of ion species for the surface activated bonding of GaAs wafers on the characteristics of the bonded interfaces. , 2015, , .		2
63	Absorption enhancement through Fabry-Pérot resonant modes in a 430-nm thick InGaAs/GaAsP multiple quantum wells solar cell. Applied Physics Letters, 2015, 106, .	1.5	33
64	Thickness-modulated InGaAs/GaAsP superlattice solar cells on vicinal substrates. Journal of Applied Physics, 2015, 117, .	1.1	12
65	Comparison of Electron and Hole Mobilities in Multiple-Quantum-Well Solar Cells Using a Time-of-Flight Technique. IEEE Journal of Photovoltaics, 2015, 5, 1613-1620.	1.5	12
66	Quantitative optical measurement of chemical potentials in intermediate band solar cells. Journal of Photonics for Energy, 2015, 5, 053092.	0.8	7
67	Surface activated Ge/GaAs wafer bonding for multi-junction solar cells. , 2014, , .		3
68	Hyperspectral Imaging of Photovoltaic Conversion " ERRATUM. Materials Research Society Symposia Proceedings, 2014, 1670, 1.	0.1	0
69	InGaAs/GaAsP superlattice solar cells with reduced carbon impurity grown by low-temperature metal-organic vapor phase epitaxy using triethylgallium. Journal of Applied Physics, 2014, 116, .	1.1	14
70	InGaAs/GaAsP strain balanced multi-quantum wires grown on misoriented GaAs substrates for high efficiency solar cells. Applied Physics Letters, 2014, 105, 083124.	1.5	26
71	Growth of InGaAs/GaAsP multiple quantum well solar cells on mis-orientated GaAs substrates. Journal of Applied Physics, 2014, 115, 233104.	1.1	12
72	Four-fold MQWs absorption enhancement in a 430 nm thick InGaAs/GaAsP MQWs solar cell. , 2014, , .		0

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73	Development of the monolithically interconnected InGaP/GaAs dual junction solar cell with bypass diode for ultrahigh concentrator application. , 2014, , .		1
74	100-period, 1.23-eV bandgap InGaAs/GaAsP quantum wells for high-efficiency GaAs solar cells: toward current-matched Ge-based tandem cells. Progress in Photovoltaics: Research and Applications, 2014, 22, 784-795.	4.4	77
75	Carrier Escape Time and Temperature-Dependent Carrier Collection Efficiency of Tunneling-Enhanced Multiple Quantum Well Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 607-613.	1.5	19
76	Plasma etching antireflection nanostructures on optical elements in concentrator photovoltaic systems. Journal of Photonics for Energy, 2014, 5, 057006.	0.8	3
77	Hyperspectral Imaging of Photovoltaic Conversion. Materials Research Society Symposia Proceedings, 2014, 1670, 57.	0.1	1
78	Carrier Time-of-Flight Measurement Using a Probe Structure for Direct Evaluation of Carrier Transport in Multiple Quantum Well Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 1518-1525.	1.5	13
79	Characterization of Photovoltaic Absorbers for High Throughput Processing. Materials Research Society Symposia Proceedings, 2014, 1709, 24.	0.1	0
80	Strain effect for different phosphorus content of InGaAs/GaAsP super-lattice in GaAs "n single junction solar cell. Journal of Crystal Growth, 2014, 401, 712-716.	0.7	10
81	Directly bonded Ge/GaAs by surface activated bonding for high efficiency III–V multi-junction solar cells. , 2014, , .		0
82	Evaluation of Carrier Collection Efficiency in Multiple Quantum Well Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 237-243.	1.5	31
83	Thin-Film InGaAs/GaAsP MQWs Solar Cell With Backside Nanoimprinted Pattern for Light Trapping. IEEE Journal of Photovoltaics, 2014, 4, 1086-1090.	1.5	14
84	High-Aspect Ratio Structures for Efficient Light Absorption and Carrier Transport in InGaAs/GaAsP Multiple Quantum-Well Solar Cells. IEEE Journal of Photovoltaics, 2013, 3, 859-867.	1.5	22
85	Fabrication of broadband antireflection structures on glass substrates by Reactive Ion Etching for application on homogenizers in CPV systems. , 2013, , .		0
86	Metalorganic vapor phase epitaxy growth of dual junction solar cell with InGaAs/GaAsP superlattice on Ge. , 2013, , .		0
87	Comprehensive validation of Carrier Collection Efficiency in multiple quantum well solar cells: For more effective and direct evaluation of carrier transport dynamics. , 2013, , .		3
88	A quantum-well superlattice solar cell for enhanced current output and minimized drop in open-circuit voltage under sunlight concentration. Journal Physics D: Applied Physics, 2013, 46, 024001.	1.3	39
89	Optimized interfacial management for InGaAs/GaAsP strain-compensated superlattice structure. Journal of Crystal Growth, 2013, 370, 157-162.	0.7	12
90	Effect of GaAs Step Layer Thickness in InGaAs/GaAsP Stepped Quantum-Well Solar Cell. IEEE Journal of Photovoltaics, 2013, 3, 289-294.	1.5	11

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91	Characteristics of hydrogen generation from water splitting by polymer electrolyte electrochemical cell directly connected with concentrated photovoltaic cell. International Journal of Hydrogen Energy, 2013, 38, 14424-14432.	3.8	89
92	Analysis for current-voltage characteristics of the InGaAs/GaAsP super-lattice solar cells under optical concentration. , 2013, , .		1
93	Performance of monolithic integrated series-connected GaAs solar cells under concentrated light. , 2013, , .		2
94	Over 12% Light to Hydrogen Energy Conversion Efficiency of Hydrogen Generation from Water: New System Concept, Concentrated Photovoltaic Electrochemical Cell (CPEC). Materials Research Society Symposia Proceedings, 2013, 1491, 52.	0.1	1
95	Carrier collection efficiency in multiple quantum well solar cells. , 2013, , .		2
96	A superlattice solar cell for enhanced current output and minimized drop in open-circuit voltage under sunlight concentration. , 2013, , .		1
97	Evaluation of asymmetric tunneling-assisted structure for InGaAs/GaAsP MQWs solar cell. , 2013, , .		0
98	Compensation doping in InGaAs / GaAsP multiple quantum well solar cells for efficient carrier transport and improved cell performance. Journal of Applied Physics, 2013, 114, .	1.1	25
99	High-aspect-ratio structures for efficient light absorption and carrier transport in InGaAs/GaAsP multiple quantum well solar cells. , 2013, , .		0
100	Effects of Strain on the Performance of InGaAs/GaAsP Multiple-Quantum-Well Solar Cells Correlated with In situ Curvature Monitoring. Applied Physics Express, 2012, 5, 062301.	1.1	9
101	Strain-Balanced InGaAs/GaAsP Superlattice Solar Cell with Enhanced Short-Circuit Current and a Minimal Drop in Open-Circuit Voltage. Applied Physics Express, 2012, 5, 052301.	1.1	5
102	Fabrication of Monolithic Integrated Series-Connected GaAs Photovoltaic Cells for Concentrator Applications. Japanese Journal of Applied Physics, 2012, 51, 10ND18.	0.8	8
103	Carrier sweep-out time in InGaAs/GaAsP multiple quantum well solar cells by time-resolved photoluminescence: effects of well depth and barrier thickness. , 2012, , .		1
104	Efficiency simulations of top surface light management structures for concentrator solar cells using RCWA and detailed balance theory. , 2012, , .		0
105	Impact of Strain Accumulation on InGaAs/GaAsP Multiple-Quantum-Well Solar Cells: Direct Correlation between In situ Strain Measurement and Cell Performances. Japanese Journal of Applied Physics, 2012, 51, 10ND16.	0.8	7
106	Effects of Background Zn Doping on the Performance of InGaAs/GaAsP Multiple Quantum Well Solar Cells Grown by a Planetary Metal Organic Vapor Phase Epitaxy Reactor. Japanese Journal of Applied Physics, 2012, 51, 10ND15.	0.8	1
107	Optimization of Gas-Switching Sequence for InGaAs/GaAsP Superlattice Structures Using In situ Wafer Curvature Monitoring. Japanese Journal of Applied Physics, 2012, 51, 10ND09.	0.8	3
108	Effect of Quantum Well on the Efficiency of Carrier Collection in InGaAs/GaAsP Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND04.	0.8	14

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109	A multi-step superlattice solar cell with enhanced subband absorption and open circuit voltage. , 2012, , .		0
110	InGaAs/GaAsP asymmetric quantum wells for enhancing carrier escape through resonant tunneling. , 2012, , .		2
111	Exploring the potential of quantum wells for efficiency enhancement in photovoltaic cells. Proceedings of SPIE, 2012, , .	0.8	2
112	Open-circuit-voltage enhancement of the III-V super-lattice solar cells under optical concentration. , 2012, , .		5
113	Enhanced Carrier Escape in MSQW Solar Cell and Its Impact on Photovoltaics Performance. IEEE Journal of Photovoltaics, 2012, 2, 221-226.	1.5	7
114	A Superlattice Solar Cell With Enhanced Short-Circuit Current and Minimized Drop in Open-Circuit Voltage. IEEE Journal of Photovoltaics, 2012, 2, 387-392.	1.5	20
115	Photocurrent Generation by Two-Step Photon Absorption With Quantum-Well Superlattice Cell. IEEE Journal of Photovoltaics, 2012, 2, 298-302.	1.5	20
116	Electrical conduction property at InAs/Si(111) interface by selective-area MOVPE. , 2012, , .		1
117	InGaAs/GaAsP quantum-well superlattice solar cell for better carrier collection and higher efficiency. , 2012, , .		0
118	Light trapping structure with backside scatterer for enhanced photo-absorption by quantum structures. , 2012, , .		3
119	High-aspect-ratio structures for efficient light absorption and carrier transport in InGaAs/GaAsP multiple quantum well solar cells. , 2012, , .		3
120	Suppressed lattice relaxation during InGaAs/GaAsP MQW growth with InGaAs and GaAs ultra-thin interlayers. Journal of Crystal Growth, 2012, 352, 239-244.	0.7	37
121	Effect of hetero-interfaces on in situ wafer curvature behavior in InGaAs/GaAsP strain-balanced MQWs. Journal of Crystal Growth, 2012, 352, 245-248.	0.7	16
122	Effect of Quantum Well on the Efficiency of Carrier Collection in InGaAs/GaAsP Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND04.	0.8	27
123	Optimization of Gas-Switching Sequence for InGaAs/GaAsP Superlattice Structures Using In situ Wafer Curvature Monitoring. Japanese Journal of Applied Physics, 2012, 51, 10ND09.	0.8	2
124	Effects of Background Zn Doping on the Performance of InGaAs/GaAsP Multiple Quantum Well Solar Cells Grown by a Planetary Metal Organic Vapor Phase Epitaxy Reactor. Japanese Journal of Applied Physics, 2012, 51, 10ND15.	0.8	1
125	Impact of Strain Accumulation on InGaAs/GaAsP Multiple-Quantum-Well Solar Cells: Direct Correlation between In situ Strain Measurement and Cell Performances. Japanese Journal of Applied Physics, 2012, 51, 10ND16.	0.8	7
126	Fabrication of graded refractive index 3-dimensional anti-reflection structure using self-assembled SiO ₂ nano particles. , 2011, , .		0

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127	Electrical and Photoconductive Properties at 1.8 K of Germanium p ⁺ -i Junction Device Fabricated by Surface-Activated Wafer Bonding. Japanese Journal of Applied Physics, 2011, 50, 066503.	0.8	2
128	Microscopy and Electrical Properties of Ge/Ge Interfaces Bonded by Surface-Activated Wafer Bonding Technology. Japanese Journal of Applied Physics, 2011, 50, 015701.	0.8	10
129	Effect of GaAs Step Layer on InGaAs/GaAsP Quantum Well Solar Cells. Applied Physics Express, 2011, 4, 122301.	1.1	14
130	Strain-compensation measurement and simulation of InGaAs/GaAsP multiple quantum wells by metal organic vapor phase epitaxy using wafer-curvature. Journal of Applied Physics, 2011, 110, .	1.1	21
131	Microscopy and Electrical Properties of Ge/Ge Interfaces Bonded by Surface-Activated Wafer Bonding Technology. Japanese Journal of Applied Physics, 2011, 50, 015701.	0.8	10
132	Electrical and Photoconductive Properties at 1.8 K of Germanium p ⁺ -i Junction Device Fabricated by Surface-Activated Wafer Bonding. Japanese Journal of Applied Physics, 2011, 50, 066503.	0.8	8
133	Development of Germanium BIB detector with surface activated bonding and Molecular-Beam Epitaxial crystal growth. , 2010, , .		2
134	Self-assembled SiO ₂ particle coating on 2 layer anti-reflection films for efficiency enhancement of GaAs PV cells. , 2010, , .		0
135	Background-limited operation of 4K-cryocooled THz photoconductive detector system with a wide frequency range of 0.8 to 4THz. , 2009, , .		2
136	Antibacterial Effects of Unripe Cephalotaxus harringtonia Fruit Extract on Gram-positive Bacteria. Journal of the Japanese Society for Food Science and Technology, 2009, 56, 533-540.	0.1	3
137	Development of the GaAs-based THz Photoconductor and Balloon-borne Experiment Module TG-ZERO. , 2009, , .		0
138	GaAs:Se and GaAs:Te Photoconductive Detectors in 300 Åµm Region for Astronomical Observations. Japanese Journal of Applied Physics, 2008, 47, 8261-8264.	0.8	17
139	Fabrication of the GaAs based terahertz photoconductors and the photometer for Tera-GATE. , 2008, , .		4
140	Optical design of image stabilizing Cassegrain-like balloon-borne telescope. Proceedings of SPIE, 2008, , .	0.8	0
141	THz balloon-borne telescope: Tera-GATE project. , 2008, , .		0
142	GaAs extrinsic photoconductors for the terahertz astronomy. , 2007, , .		1
143	Development of GaAs photoconductors for far-infrared/submillimeter astronomy. , 2004, 5498, 637.		1
144	Smooth surface morphology and long carrier lifetime of InGaP realized by low-temperature-grown cover layer. Physica Status Solidi (B): Basic Research, 0, , .	0.7	1

#	ARTICLE	IF	CITATIONS
145	Enhanced Radiative Efficiency of InGaAs/GaAsP Multiple Quantum Wells by Optimizing the Thickness of Interlayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 0, , .	0.8	0